

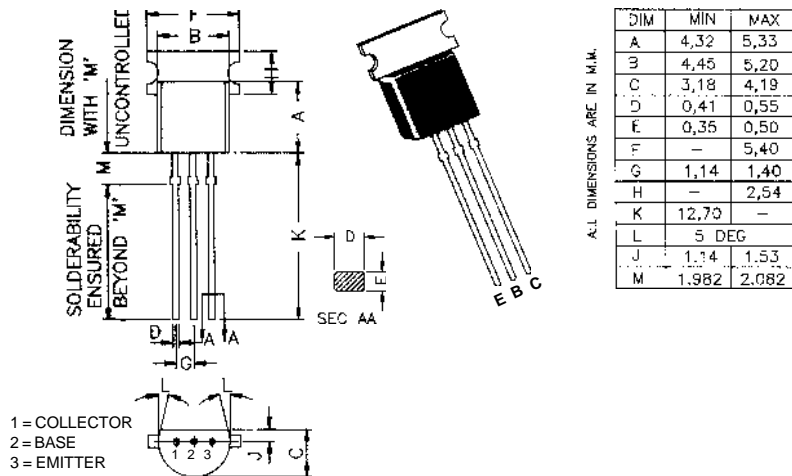
TO-237 Plastic Package

**CTN635, CTN637, CTN639
CTN636, CTN638, CTN640**

CTN635, 637, 639 NPN SILICON PLANAR EPITAXIAL TRANSISTORS

CTN636, 638, 640 PNP SILICON PLANAR EPITAXIAL TRANSISTORS

Complementary Transistors in Plastic Package for Driver Stage of Audio Amplifier.



A.L. DIMENSIONS ARE IN M.M.

DIM	MIN	MAX
A	4,32	5,33
B	4,45	5,20
C	3,18	4,19
D	0,41	0,55
E	0,35	0,50
F	-	5,40
G	1,14	1,40
H	-	2,54
K	12,70	-
L	5 DEG	
J	1,14	1,53
M	1,982	2,082

ABSOLUTE MAXIMUM RATINGS

Ratings	Symbol	CTN635	CTN637	CTN639	Units
		CTN636	CTN638	CTN640	
Collector-Base Voltage	V_{CBO}	45	60	100	V
Collector-Emitter Voltage	V_{CEO}	45	60	80	V
Emitter-Base Voltage	V_{EBO}	-	5	-	V
Collector Current - Continuous	I_C	-	1	-	A
Peak	I_{CM}	-	1.5	-	A
Base Current - Continuous	I_B	-	100	-	mA
Peak	I_{BM}	-	200	-	mA
Power Dissipation @ $T_a=25^\circ C$	P_D	-	750	-	mW
Derate above $25^\circ C$	-	-	6	-	mW/°C
Power Dissipation @ $T_c=25^\circ C$	P_D	-	2.5	-	W
Derate above $25^\circ C$	-	-	20	-	mW/°C
Operating And Storage Junction Temperature Range	T_j, T_{stg}	-	-55 to +150		°C

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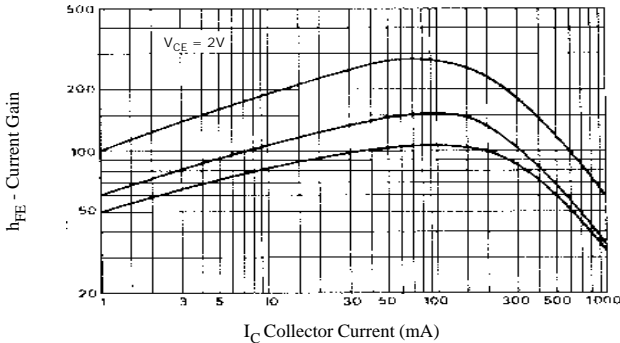
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Voltage $I_C=10\text{mA}, I_B=0$	BV_{CEO}	45	-	-	V
		60	-	-	V
		80	-	-	V
Collector-Base Voltage $I_C=100\mu\text{A}, I_E=0$	BV_{CBO}	45	-	-	V
		60	-	-	V
		100	-	-	V
Emitter-Base Voltage $I_E=10\mu\text{A}, I_C=0$	BV_{EBO}	5	-	-	V
Collector Cutoff Current $V_{CB}=30\text{V}, I_E=0$	I_{CBO}	-	-	100	nA
$V_{CB}=30\text{V}, I_E=0, T_a=125^\circ\text{C}$		-	-	10	μA
Base Emitter On Voltage $I_C=500\text{mA}, V_{CE}=2\text{V}$	$V_{BE(on)}^*$	-	-	1.0	V
Collector-Emitter (Sat) Voltage $I_C=500\text{mA}, I_B=50\text{mA}$	$V_{CE(sat)}^*$	-	-	0.5	V
D.C. Current Gain $I_C=5\text{mA}, V_{CE}=2\text{V}$	h_{FE}	25	-	-	
$I_C=150\text{mA}, V_{CE}=2\text{V}^*$		40	-	160	
		40	-	160	
$I_C=500\text{mA}, V_{CE}=2\text{V}^*$		25	-	-	
DYNAMIC CHARACTERISTICS					
Input Capacitance $V_{BE}=0.5\text{V}, I_C=0,$ $f=1\text{MHz}$	C_{ib}	-	50	-	pF
		-	110	-	pF
Input Capacitance $V_{CB}=10\text{V}, I_C=0,$ $f=1\text{MHz}$	C_{ob}	-	7	-	pF
		-	9	-	pF
Transition Frequency $I_C=10\text{mA}, V_{CE}=5\text{V},$ $f=35\text{MHz}$	f_T	-	130	-	MHz
		-	50	-	MHz

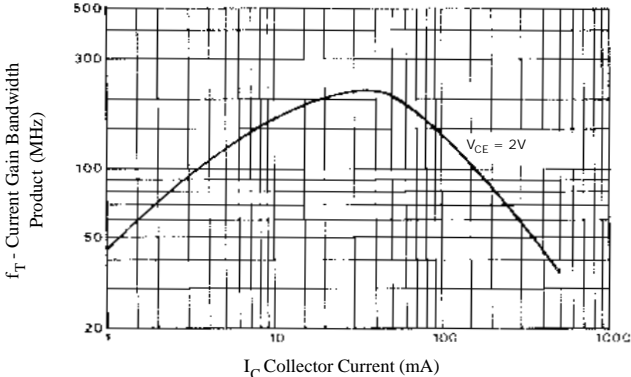
* Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

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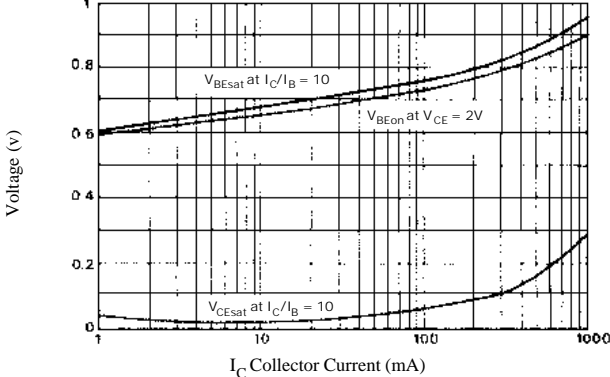
DC Current Gain



Current Gain Bandwidth Product



Saturation and On Voltages



Disclaimer

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